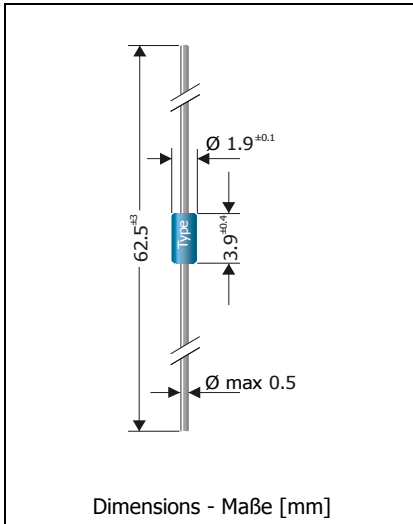


DB3 , DB4 , DB31 , DB32

Bidirectional Si-Trigger-Diodes (DIAC) Bidirektionale Si-Triggerdioden (DIAC)

Version 2012-07-03



Breakover voltage Durchbruchspannung	28 ... 45 V
Peak pulse current Max. Triggerimpuls	± 2 A
Glass case Glas-Gehäuse	~ DO-35 ~ SOD-27
Weight approx. Gewicht ca.	0.13 g
Standard packaging taped in ammo pack Standard Lieferform gegurtet in Ammo-Pack	



Maximum ratings	Grenzwerte		
Power dissipation Verlustleistung	$T_A = 50^\circ\text{C}$	P_{tot}	150 mW ¹⁾
Peak pulse current (120 Hz pulse repetition rate) Max. Triggerstrom (120 Hz Puls-Wiederholrate)	$t_p \leq 10 \mu\text{s}$	I_{PM}	± 2 A ¹⁾
Operating Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_s	-50...+100°C -50...+175°C

Characteristics	Kennwerte			
Breakover voltage Durchbruchspannung	$dV/dt = 10 \text{ V}/\mu\text{s}$	DB3 DB31 DB32 DB4	V_{BO} V_{BO} V_{BO} V_{BO}	28 ... 36 V 30 ... 34 V 32 ... 36 V 35 ... 45 V
Breakover current – Durchbruchstrom		$V = 98\% V_{\text{BO}}$	I_{BO}	< 200 μA
Asymmetry of breakover voltage Unsymmetrie der Durchbruchspannung		$ V_{(\text{BO})\text{F}} - V_{(\text{BO})\text{R}} $	ΔV_{BO}	< 3.8 V
Foldback voltage – Spannungs-Rücksprung $\Delta I = I_{\text{BO}}$ to/auf $I_{\text{F}} = 10 \text{ mA}$		$dV/dt = 10 \text{ V}/\mu\text{s}$	$\Delta V_{\text{F/R}}$	> 5 V
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft			R_{thA}	< 300 K/W ¹⁾

¹ Valid, if leads are kept at ambient temperature at a distance of 10 mm from case
Gültig, wenn die Anschlussdrähte in 10 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

